

Nikolai Yarykin

List of Publications by Year in descending order

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| # | ARTICLE | IF | CITATIONS |
|----|--|-----|-----------|
| 1 | The Cu photoluminescence defect and the early stages of Cu precipitation in Si. Journal of Applied Physics, 2020, 127, . | 2.5 | 5 |
| 2 | Room-temperature Ni Interaction with Deformation-Induced Defects in Si: A DLTS Study. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1900326. | 1.8 | 3 |
| 3 | Electrically Active Copper-Nickel Complexes in p-type Silicon. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1900304. | 1.8 | 4 |
| 4 | Nickel Interaction with Vacancy-type Radiation Defects in Silicon. Physica Status Solidi - Rapid Research Letters, 2019, 13, 1800651. | 2.4 | 2 |
| 5 | Deep level centers in electron-irradiated silicon crystals doped with copper at different temperatures. Physica Status Solidi C: Current Topics in Solid State Physics, 2017, 14, 1600267. | 0.8 | 3 |
| 6 | Nickel in silicon: Room-temperature in-diffusion and interaction with radiation defects. Physica Status Solidi C: Current Topics in Solid State Physics, 2017, 14, 1700005. | 0.8 | 6 |
| 7 | Dislocation trails in Si: Geometry and electrical properties. Physica Status Solidi C: Current Topics in Solid State Physics, 2017, 14, 1700074. | 0.8 | 5 |
| 8 | Evidence for room-temperature in-diffusion of nickel into silicon. Applied Physics Letters, 2016, 109, 102101. | 3.3 | 14 |
| 9 | Spatial Distribution of the Dislocation Trails in Silicon. Solid State Phenomena, 2015, 242, 155-159. | 0.3 | 5 |
| 10 | Hydrogenation of the CuPL center in silicon. Applied Physics Letters, 2014, 105, 012109. | 3.3 | 5 |
| 11 | Deep levels of copper-hydrogen complexes in silicon. Physical Review B, 2013, 88, . | 3.2 | 12 |
| 12 | Copper-related deep-level centers in irradiated p-type silicon. Physical Review B, 2011, 83, . | 3.2 | 20 |
| 13 | DLTS study of the oxygen dimer formation kinetics in silicon. Physica B: Condensed Matter, 2009, 404, 4576-4578. | 2.7 | 2 |
| 14 | Centers with low correlation energy in deep-level transient spectroscopy studies. Semiconductor Science and Technology, 2008, 23, 125031. | 2.0 | 1 |
| 15 | Properties and identification of the oxygen-related radiation defects in silicon. Physica B: Condensed Matter, 2007, 401-402, 483-486. | 2.7 | 5 |
| 16 | Oxygen gettering at defects introduced by plastic deformation in silicon. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 3070-3074. | 0.8 | 3 |
| 17 | Contribution of the disturbed dislocation slip planes to the electrical properties of plastically deformed silicon. Physica B: Condensed Matter, 2003, 340-342, 1005-1008. | 2.7 | 23 |
| 18 | On the nature of hydrogen-related centers in p-type irradiated silicon. Physica B: Condensed Matter, 2001, 308-310, 210-212. | 2.7 | 27 |

| # | ARTICLE | IF | CITATIONS |
|----|---|-----|-----------|
| 19 | The Electrical Activity of Dislocation Slip Planes in Semiconductor Crystals. Materials Science Forum, 1986, 10-12, 787-790. | 0.3 | 8 |
| 20 | Metastable Cu<i>i></i></i></i>V<i>i></i></i></i>O* Complex in Silicon. Solid State Phenomena, 0, 205-206, 255-259. | 0.3 | 5 |
| 21 | Interaction of Interstitial Copper with Isolated Vacancies in Silicon. Solid State Phenomena, 0, 242, 308-311. | 0.3 | 4 |
| 22 | Interstitial Carbon in <i>i></i></i></i>p<i>i></i></i></i>-Type Copper-Doped Silicon. Solid State Phenomena, 0, 242, 302-307. | 0.3 | 1 |
| 23 | Electrical Activation of Interstitial Ni in Cu<i>i></i></i></i>Doped Si. Physica Status Solidi (A) Applications and Materials Science, 0, , 2100135. | 1.8 | 0 |
| 24 | Copper Complexes with Carbon<i>i></i></i></i>-Related Radiation Defects in Silicon. Physica Status Solidi (A) Applications and Materials Science, 0, , 2100141. | 1.8 | 1 |